## **Supplementary Data**

## High-performance 2D/3D hybrid dimensional p-n heterojunction solar cell

with reduced recombination rate by an interfacial layer

H.H. Hegazy<sup>1,2</sup>, Amir Muhammad Afzal<sup>3</sup>, A. Dahshan<sup>1,4</sup>, Muhammad Waqas Iqbal <sup>3</sup>, Imen Kebaili<sup>1,5</sup>

<sup>1</sup> Department of Physics, Faculty of Science, King Khalid University, P.O. Box 9004, Abha, Saudi Arabia.

<sup>2</sup> Department of Physics, Faculty of Science, Al-Azhar University; 71524 Assiut ; Egypt
<sup>3</sup>Department of Physics, Riphah International University, 13 Raiwind road, Lahore, Pakistan

<sup>4</sup>Department of Physics, Faculty of Science, Port Said University, Port Said, Egypt.

<sup>5</sup>Université de Sfax, Laboratoire de Physique Appliquée, Groupe de Physique des matériaux luminescents, Faculté des Sciences de Sfax, Département de Physique, BP 1171, Université de Sfax, 3018 Sfax, Tunisie.

Corresponding author: amirafzal461@gmail.com



Figure S1. Optical image of  $MoS_2$  on the surface of p-Si



Figure S2. FE-SEM image of  $MoS_2$  on the surface of p-Si



**Figure S3.** Change in Raman shift with the annealing temperatures, (a) in-plan and (b) out of plan vibration mode



Figure S4. Raman spectroscopy measurement of h-BN



Figure S5. UV-Vis absorption spectrum of few-layered  $MoS_2$  flakes at different temperatures



**Figure S6.** (a) Schematic diagram of  $MoS_2$  field effect transistor with  $Al_2O_3$  as a layer between the metal electrode and  $MoS_2$  junction (b) Height profile to measure the thickness of  $MoS_2$  flake. The inset figure shows the atomic force microscopy image (c) Transfer curves of  $MoS_2$  FET with

and with passivation of  $Al_2O_3$  (d) Transfer curves of  $MoS_2$  FETs with different interfacial layers (e) Change in mobility of  $MoS_2$  FETs with different interfacial layers and passivation (f) Currentvoltage characteristics of  $MoS_2$  FETs with and without passivation of  $Al_2O_3$ 



**Figure S7.** Time-dependent response to measure the effect of passivation on the generation of electron-hole pairs.



**Figure S8.** Ln  $(I/V^2)$  vs. 1/V plots reconfigured from current-voltage curves which were measured at different temperatures.



Figure S9. Change in (a) Voc (b) FF